

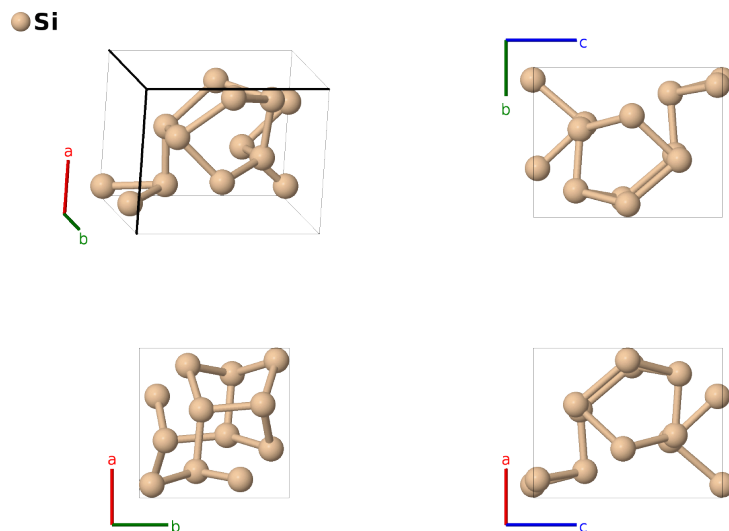
“ST12” Structure of Si: A_tP12_96_ab-001

This structure originally had the label **A.tP12_96.ab**. Calls to that address will be redirected here.

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<https://aflow.org/p/YUU3>

https://aflow.org/p/A_tP12_96_ab-001



| | |
|--------------------------------|---|
| Prototype | Si |
| AFLOW prototype label | A_tP12_96_ab-001 |
| ICSD | 16954 |
| Pearson symbol | tP12 |
| Space group number | 96 |
| Space group symbol | $P4_32_12$ |
| AFLOW prototype command | <code>aflow --proto=A_tP12_96_ab-001 --params=a, c/a, x₁, x₂, y₂, z₂</code> |

Other compounds with this structure

γ -Ge

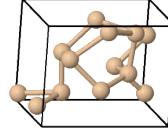
- This is a tetragonally bonded structure which packs more efficiently than diamond. It is seen experimentally in some silicon and germanium samples and is a staple for testing silicon potentials and first-principles calculations. The structure shown here is taken from the calculations in (Crain, 1994), but the ICSD entry is an experimental entry for germanium (Bundy, 1963).

Simple Tetragonal primitive vectors

$$\mathbf{a}_1 = a \hat{\mathbf{x}}$$

$$\mathbf{a}_2 = a \hat{\mathbf{y}}$$

$$\mathbf{a}_3 = c \hat{\mathbf{z}}$$



Basis vectors

| | Lattice coordinates | | Cartesian coordinates | Wyckoff position | Atom type |
|-------------------|---|-----|--|------------------|-----------|
| \mathbf{B}_1 | $= x_1 \mathbf{a}_1 + x_1 \mathbf{a}_2$ | $=$ | $ax_1 \hat{\mathbf{x}} + ax_1 \hat{\mathbf{y}}$ | (4a) | Si I |
| \mathbf{B}_2 | $= -x_1 \mathbf{a}_1 - x_1 \mathbf{a}_2 + \frac{1}{2} \mathbf{a}_3$ | $=$ | $-ax_1 \hat{\mathbf{x}} - ax_1 \hat{\mathbf{y}} + \frac{1}{2} c \hat{\mathbf{z}}$ | (4a) | Si I |
| \mathbf{B}_3 | $= -(x_1 - \frac{1}{2}) \mathbf{a}_1 + (x_1 + \frac{1}{2}) \mathbf{a}_2 + \frac{3}{4} \mathbf{a}_3$ | $=$ | $-a(x_1 - \frac{1}{2}) \hat{\mathbf{x}} + a(x_1 + \frac{1}{2}) \hat{\mathbf{y}} + \frac{3}{4} c \hat{\mathbf{z}}$ | (4a) | Si I |
| \mathbf{B}_4 | $= (x_1 + \frac{1}{2}) \mathbf{a}_1 - (x_1 - \frac{1}{2}) \mathbf{a}_2 + \frac{1}{4} \mathbf{a}_3$ | $=$ | $a(x_1 + \frac{1}{2}) \hat{\mathbf{x}} - a(x_1 - \frac{1}{2}) \hat{\mathbf{y}} + \frac{1}{4} c \hat{\mathbf{z}}$ | (4a) | Si I |
| \mathbf{B}_5 | $= x_2 \mathbf{a}_1 + y_2 \mathbf{a}_2 + z_2 \mathbf{a}_3$ | $=$ | $ax_2 \hat{\mathbf{x}} + ay_2 \hat{\mathbf{y}} + cz_2 \hat{\mathbf{z}}$ | (8b) | Si II |
| \mathbf{B}_6 | $= -x_2 \mathbf{a}_1 - y_2 \mathbf{a}_2 + (z_2 + \frac{1}{2}) \mathbf{a}_3$ | $=$ | $-ax_2 \hat{\mathbf{x}} - ay_2 \hat{\mathbf{y}} + c(z_2 + \frac{1}{2}) \hat{\mathbf{z}}$ | (8b) | Si II |
| \mathbf{B}_7 | $= -(y_2 - \frac{1}{2}) \mathbf{a}_1 + (x_2 + \frac{1}{2}) \mathbf{a}_2 + (z_2 + \frac{3}{4}) \mathbf{a}_3$ | $=$ | $-a(y_2 - \frac{1}{2}) \hat{\mathbf{x}} + a(x_2 + \frac{1}{2}) \hat{\mathbf{y}} + c(z_2 + \frac{3}{4}) \hat{\mathbf{z}}$ | (8b) | Si II |
| \mathbf{B}_8 | $= (y_2 + \frac{1}{2}) \mathbf{a}_1 - (x_2 - \frac{1}{2}) \mathbf{a}_2 + (z_2 + \frac{1}{4}) \mathbf{a}_3$ | $=$ | $a(y_2 + \frac{1}{2}) \hat{\mathbf{x}} - a(x_2 - \frac{1}{2}) \hat{\mathbf{y}} + c(z_2 + \frac{1}{4}) \hat{\mathbf{z}}$ | (8b) | Si II |
| \mathbf{B}_9 | $= -(x_2 - \frac{1}{2}) \mathbf{a}_1 + (y_2 + \frac{1}{2}) \mathbf{a}_2 - (z_2 - \frac{3}{4}) \mathbf{a}_3$ | $=$ | $-a(x_2 - \frac{1}{2}) \hat{\mathbf{x}} + a(y_2 + \frac{1}{2}) \hat{\mathbf{y}} - c(z_2 - \frac{3}{4}) \hat{\mathbf{z}}$ | (8b) | Si II |
| \mathbf{B}_{10} | $= (x_2 + \frac{1}{2}) \mathbf{a}_1 - (y_2 - \frac{1}{2}) \mathbf{a}_2 - (z_2 - \frac{1}{4}) \mathbf{a}_3$ | $=$ | $a(x_2 + \frac{1}{2}) \hat{\mathbf{x}} - a(y_2 - \frac{1}{2}) \hat{\mathbf{y}} - c(z_2 - \frac{1}{4}) \hat{\mathbf{z}}$ | (8b) | Si II |
| \mathbf{B}_{11} | $= y_2 \mathbf{a}_1 + x_2 \mathbf{a}_2 - z_2 \mathbf{a}_3$ | $=$ | $ay_2 \hat{\mathbf{x}} + ax_2 \hat{\mathbf{y}} - cz_2 \hat{\mathbf{z}}$ | (8b) | Si II |
| \mathbf{B}_{12} | $= -y_2 \mathbf{a}_1 - x_2 \mathbf{a}_2 - (z_2 - \frac{1}{2}) \mathbf{a}_3$ | $=$ | $-ay_2 \hat{\mathbf{x}} - ax_2 \hat{\mathbf{y}} - c(z_2 - \frac{1}{2}) \hat{\mathbf{z}}$ | (8b) | Si II |

References

- [1] J. Crain, S. J. Clark, G. J. Ackland, M. C. Payne, V. Milman, P. D. Hatton, and B. J. Reid, *Theoretical study of high-density phases of covalent semiconductors. I. Ab initio treatment*, Phys. Rev. B **49**, 5329–5340 (1994), doi:10.1103/PhysRevB.49.5329.
- [2] F. P. Bundy and J. S. Kasper, *A New Dense Form of Solid Germanium*, Science **139**, 340–341 (1963), doi:10.1126/science.139.3552.340.